

1/27 ZHU ET AL. JPA FIS920030371US1

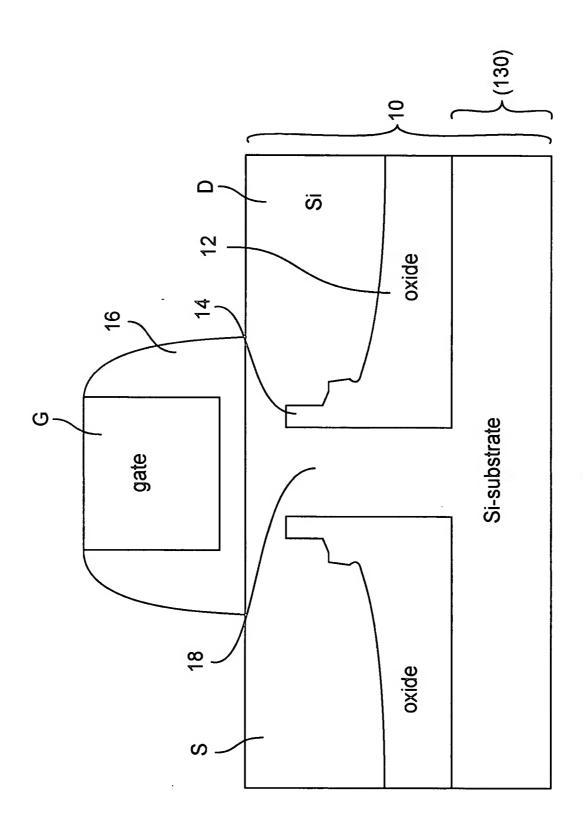


Figure 1

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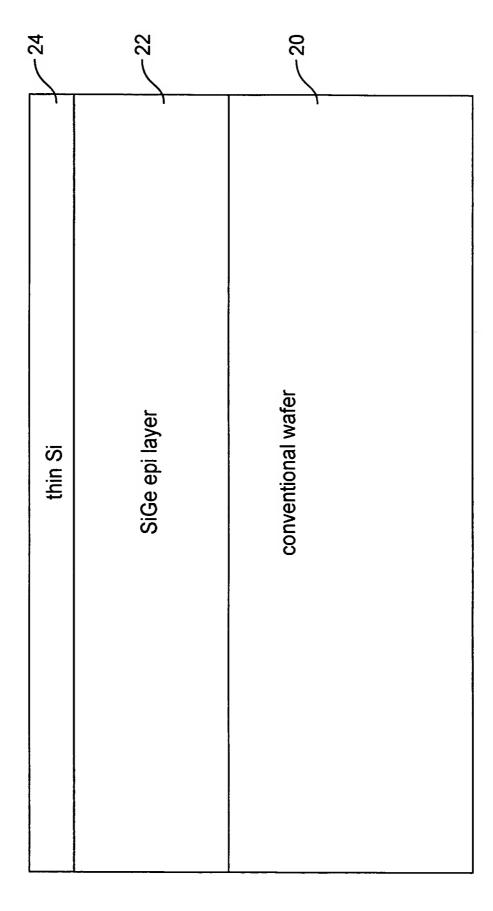
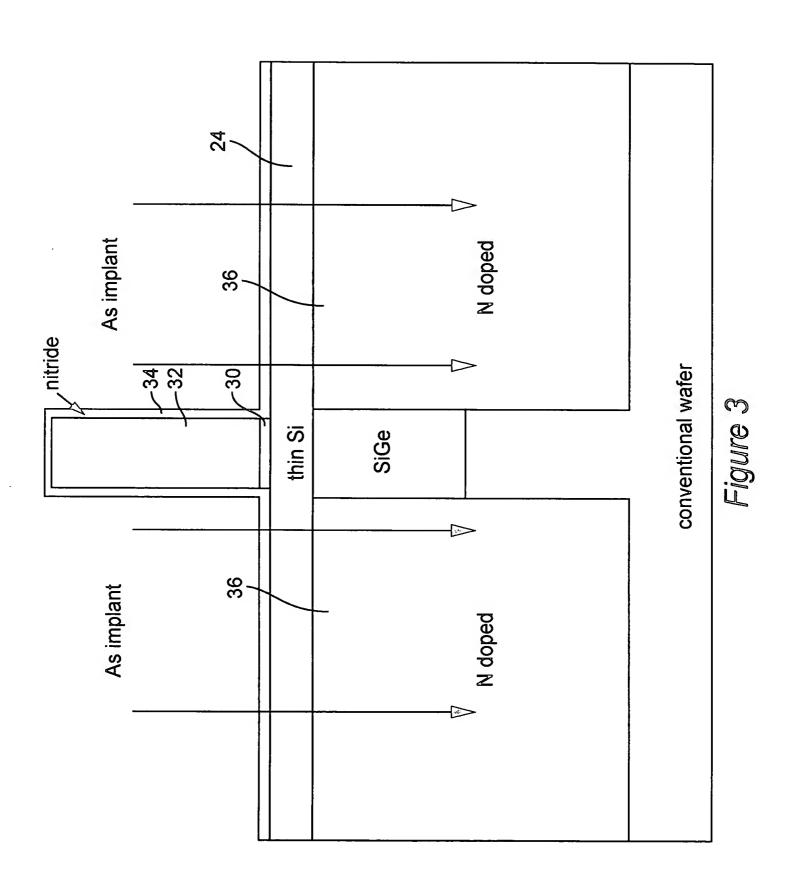
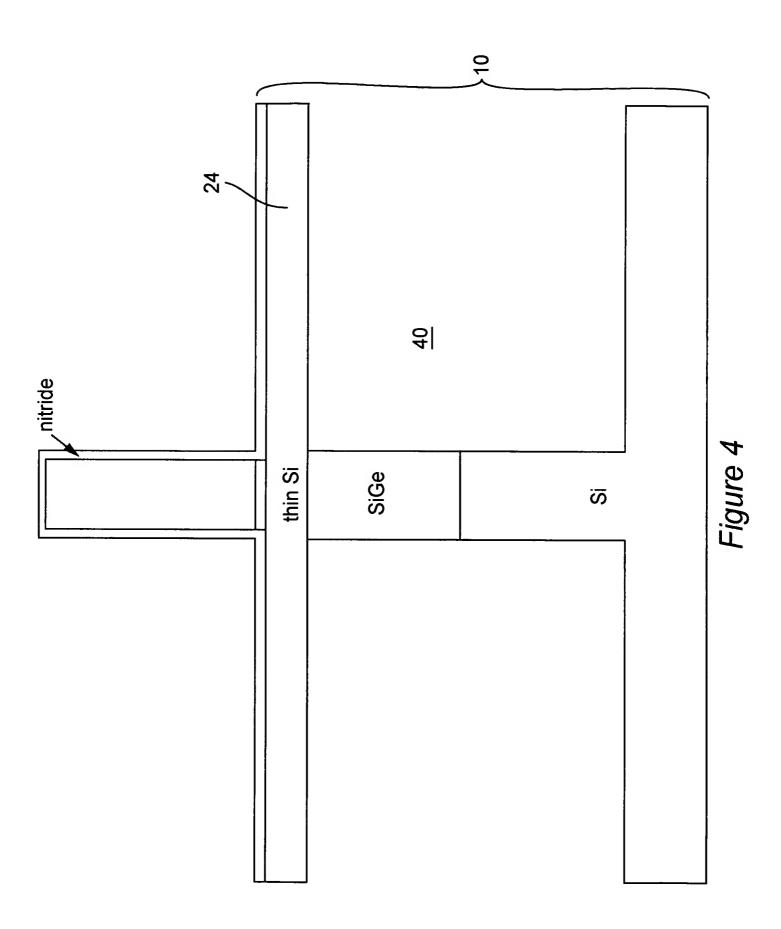


Figure 2

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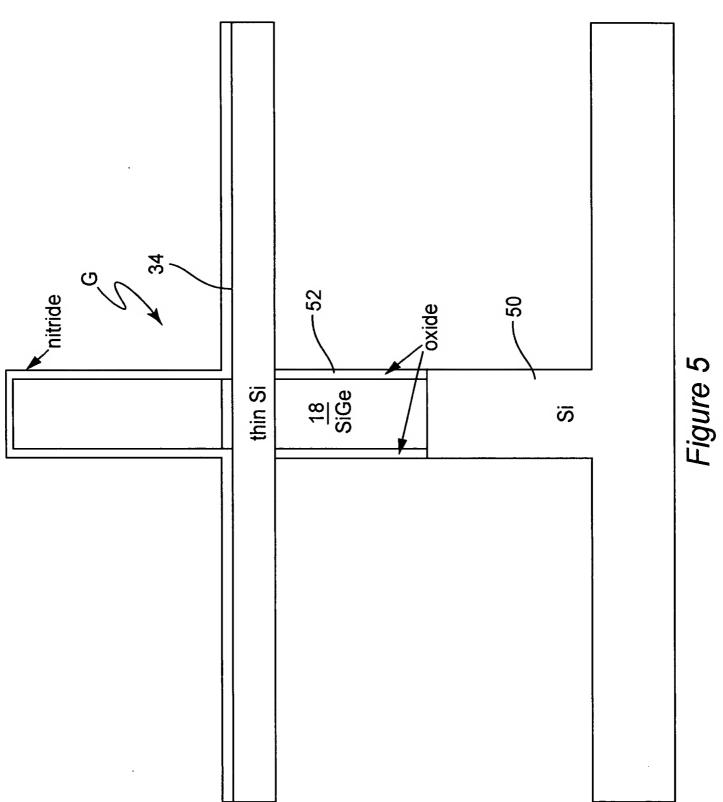


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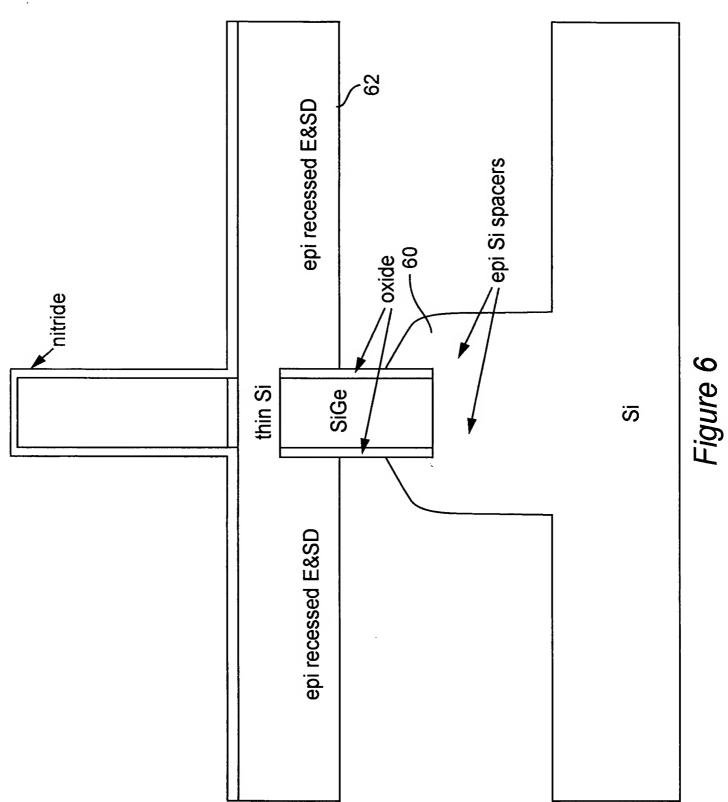


>

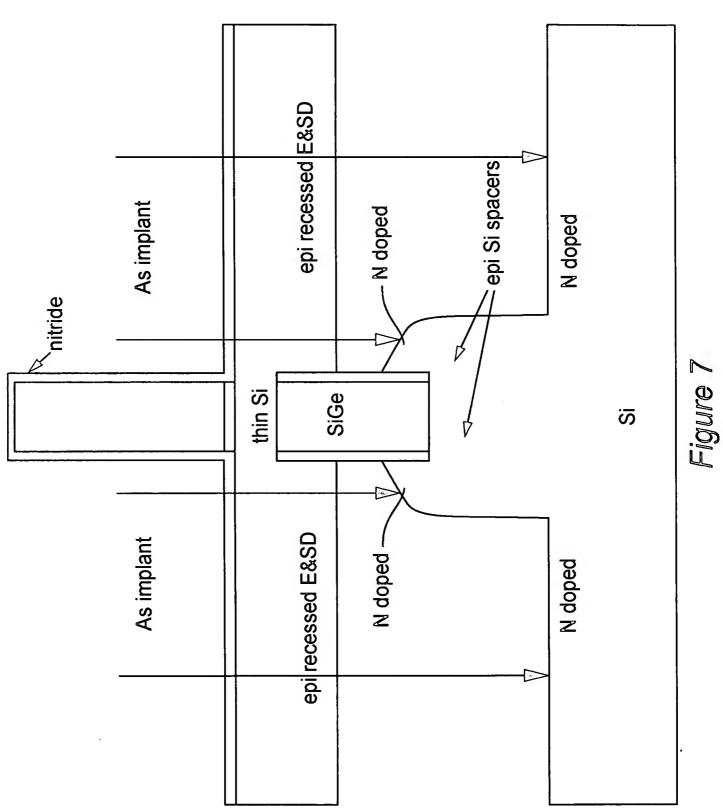
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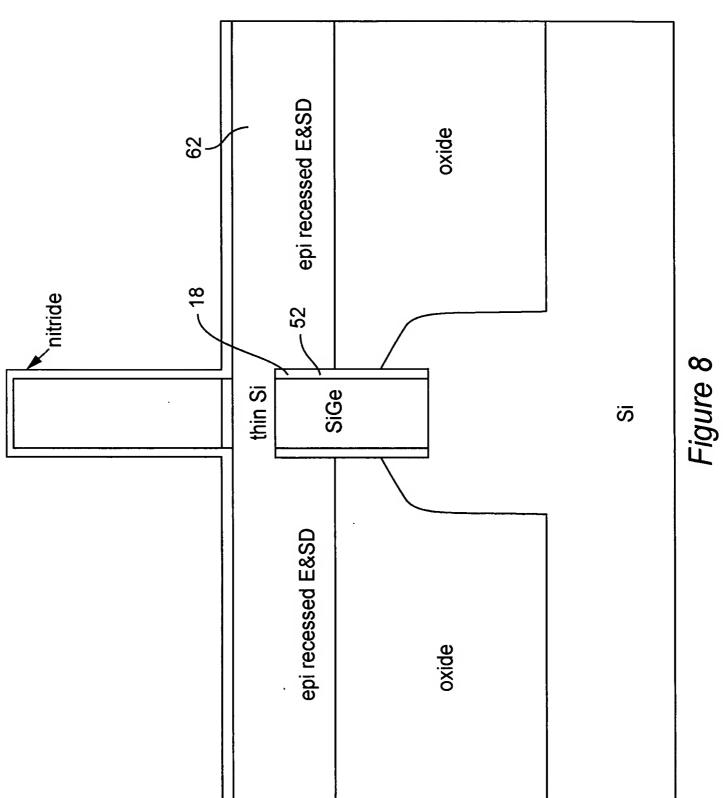
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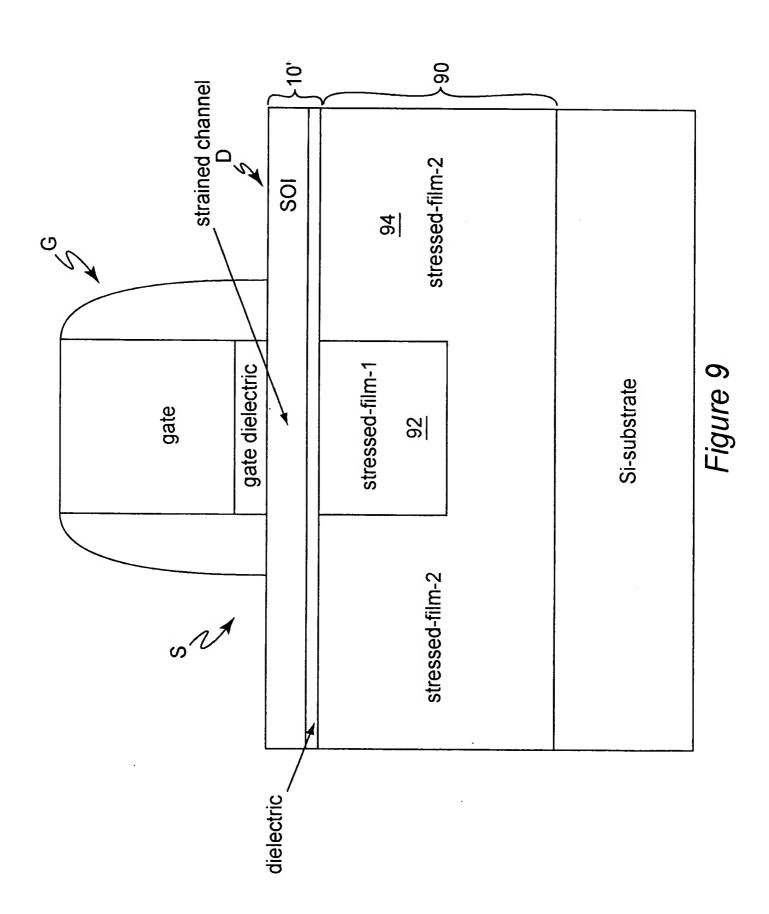
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110	ss is ~ 0.2-0.5 um)	130
iS-d	p-SiGe (for process convenience, this layer thicknes	Si substrate
		p-Si p-SiGe convenience, this layer thickness is ~ 0.2-0.5

Figure 10

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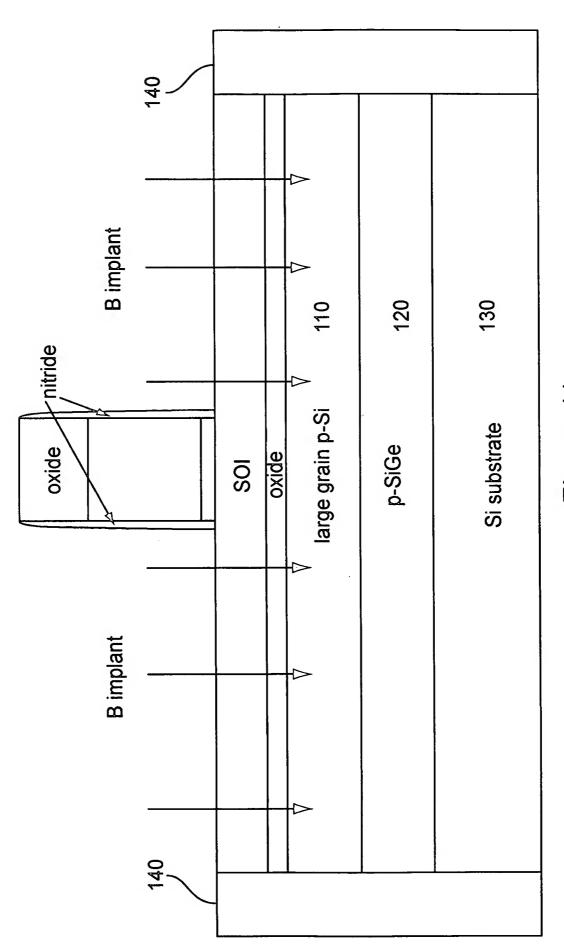
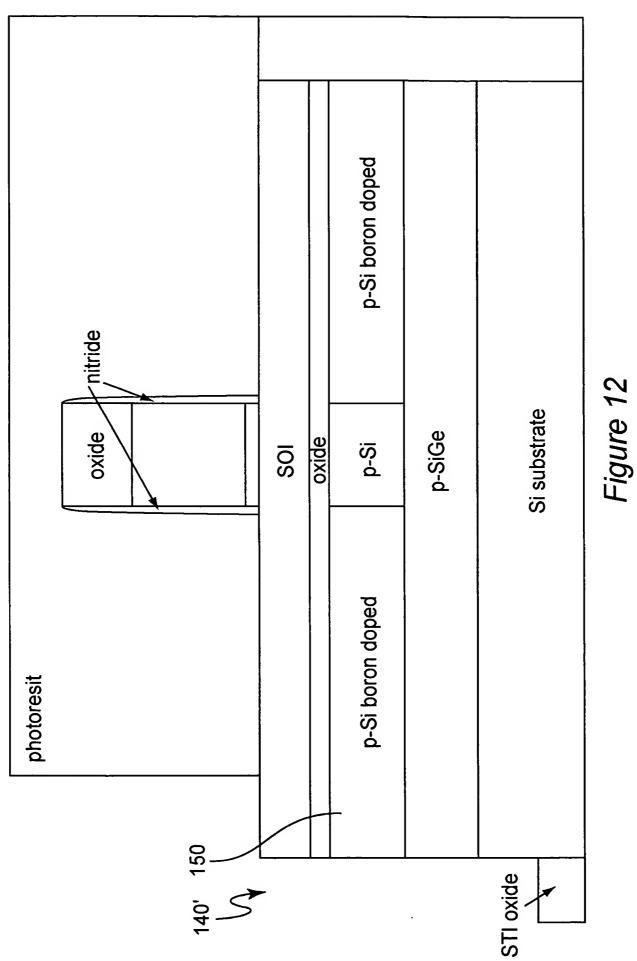
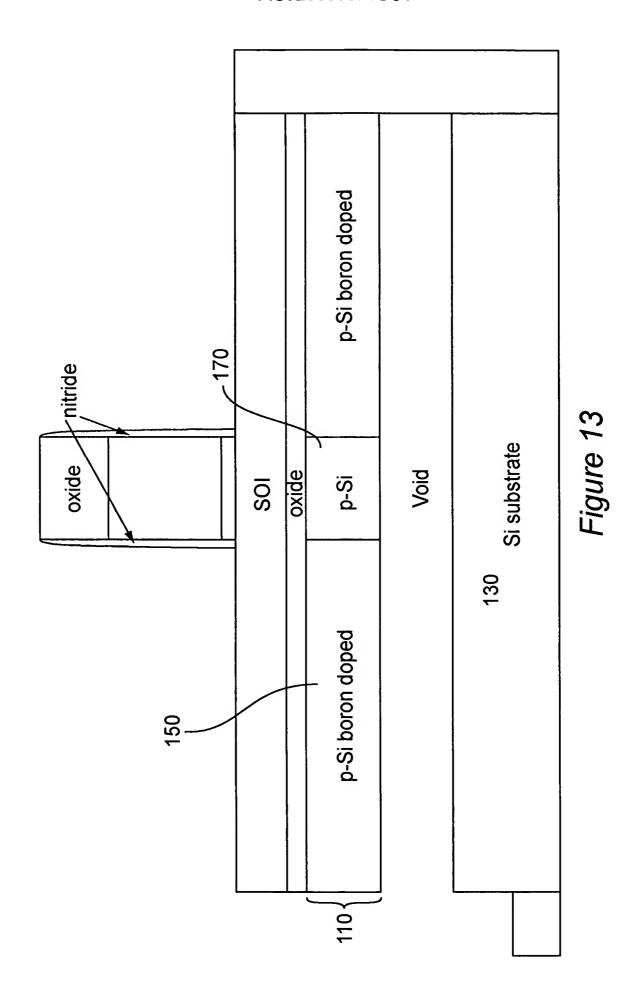


Figure 11

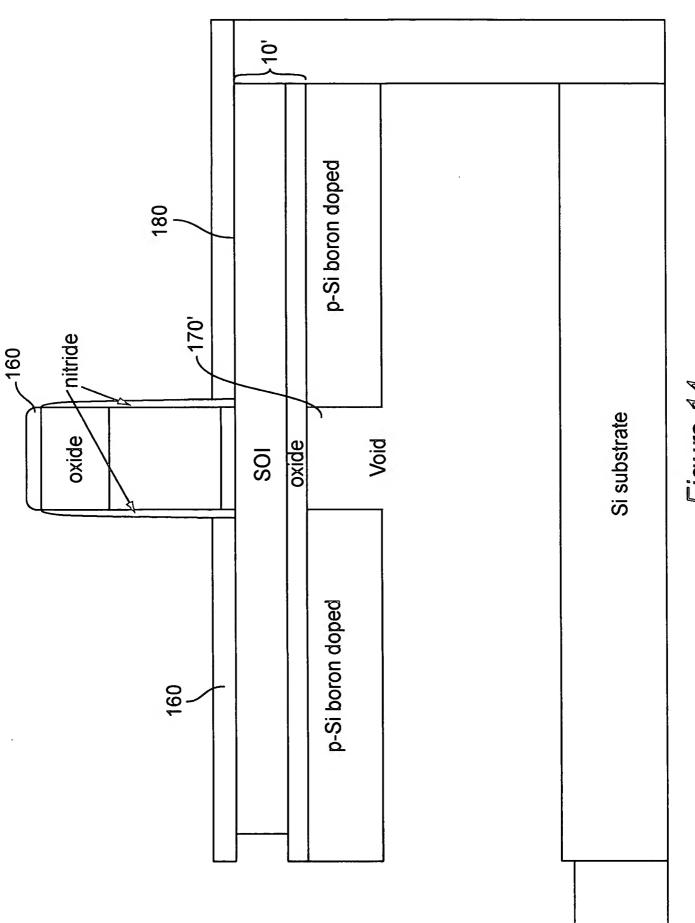
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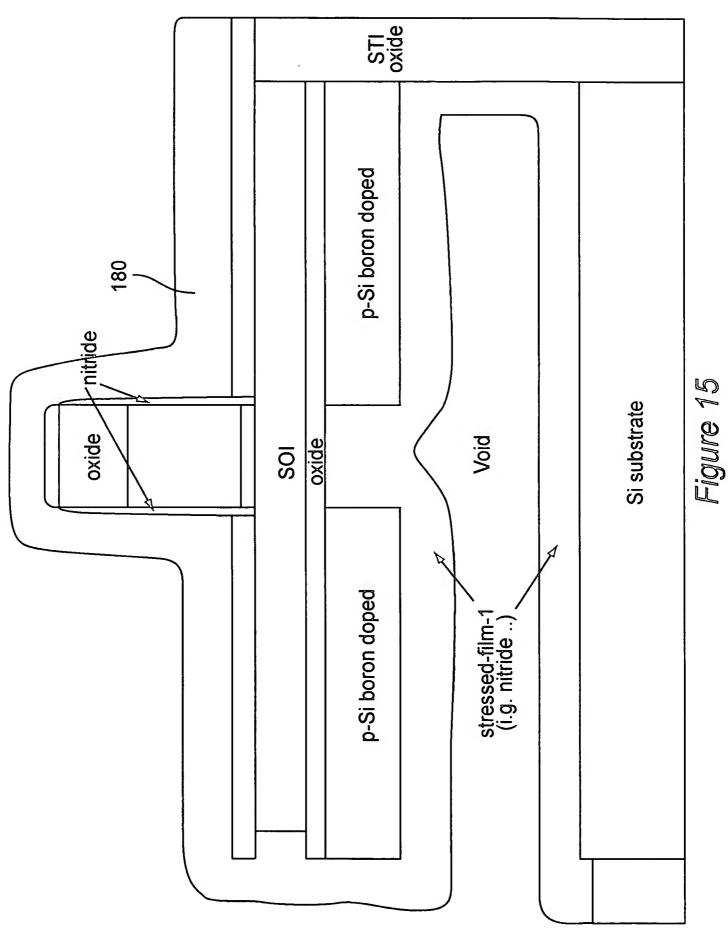
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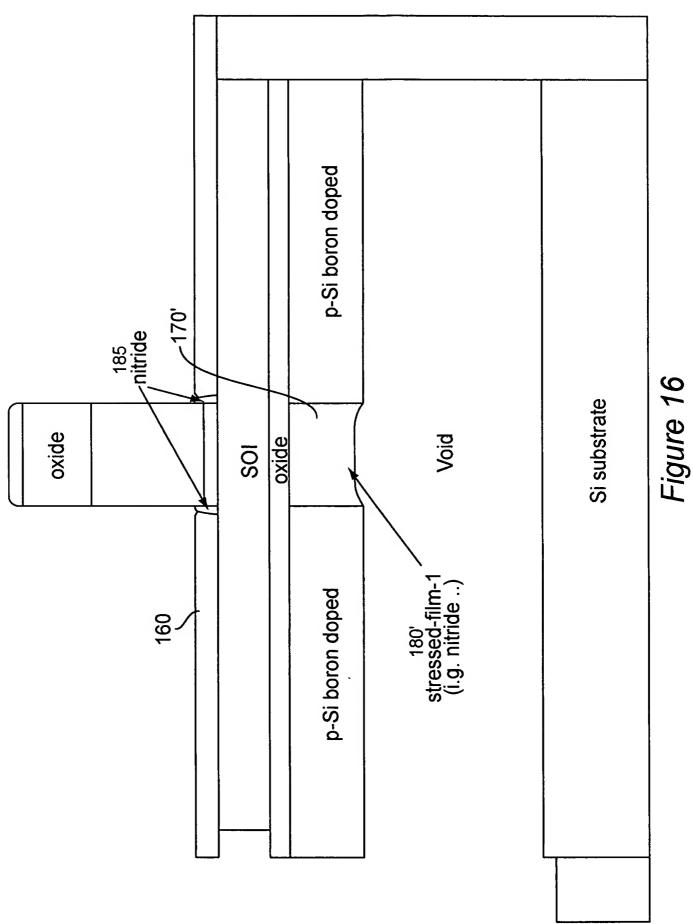
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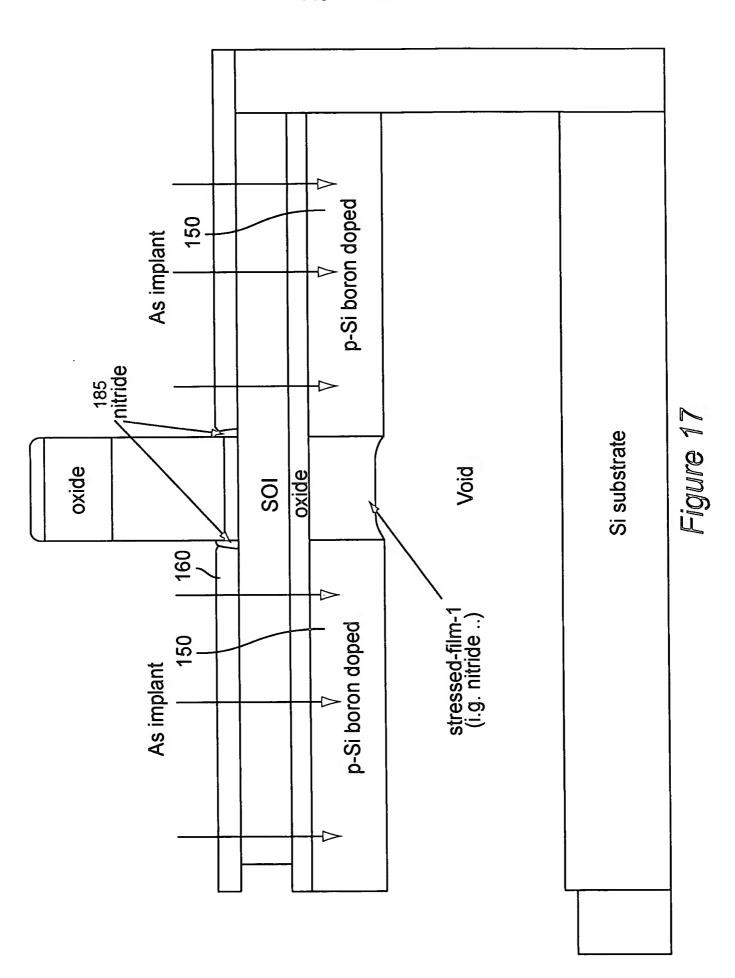
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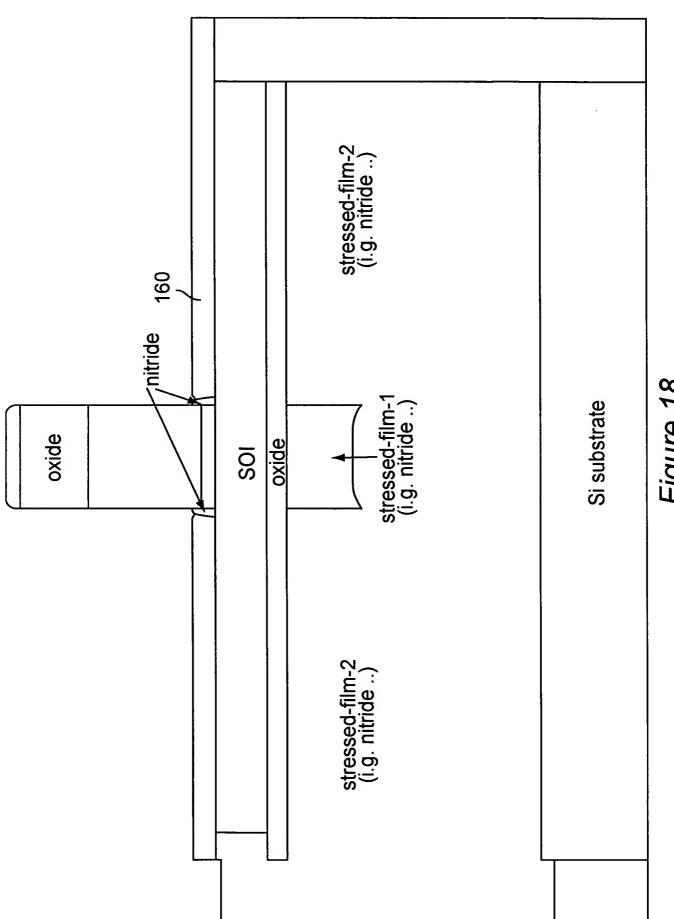
16/27 FIS920030371US1



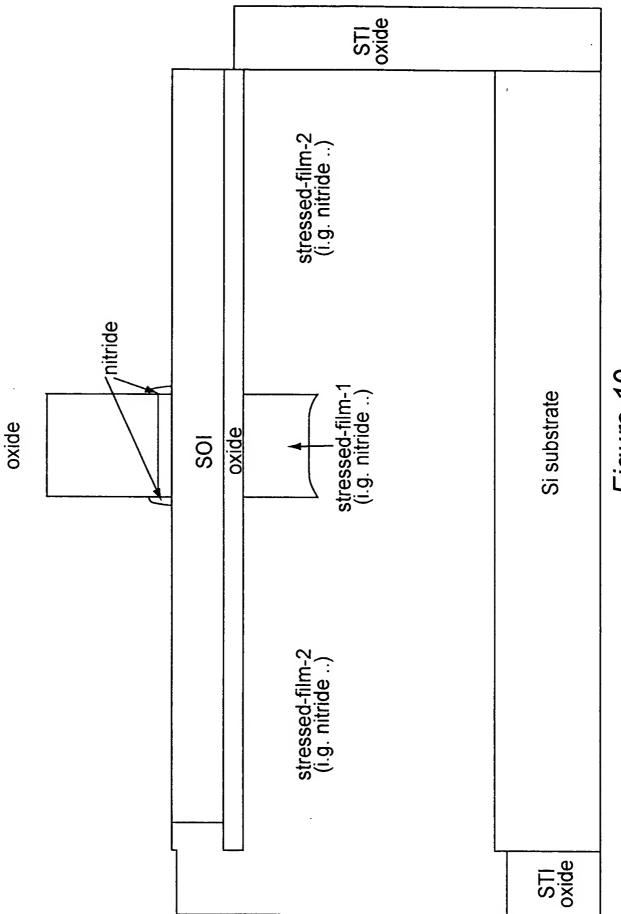
17/27 FIS920030371US1



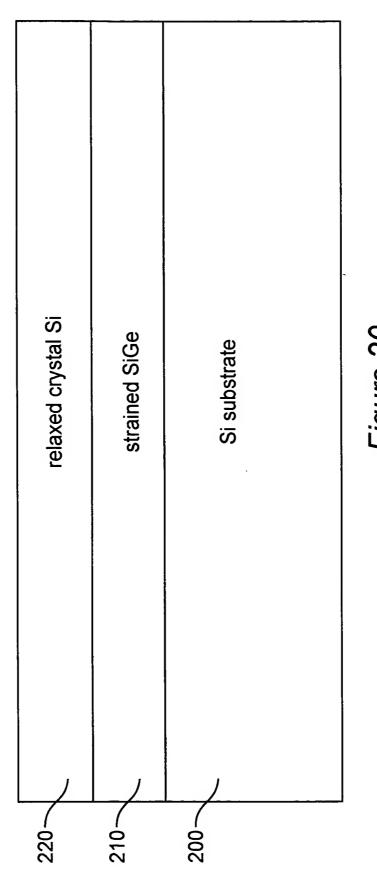
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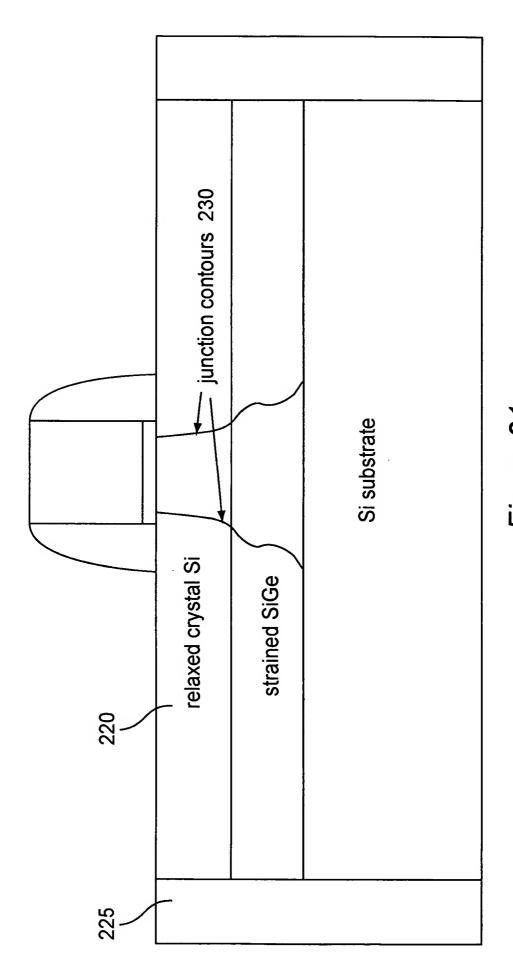


Figure 21

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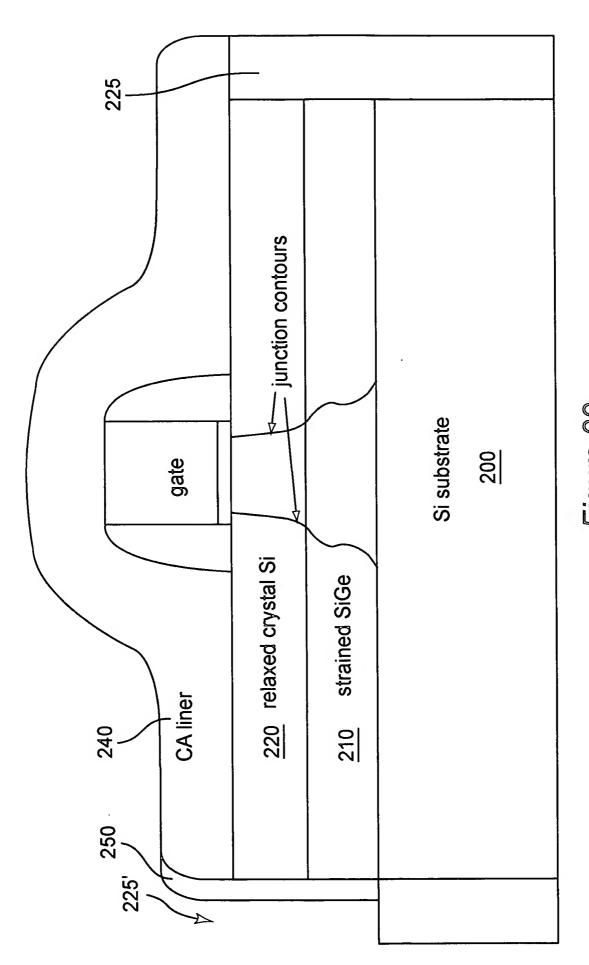
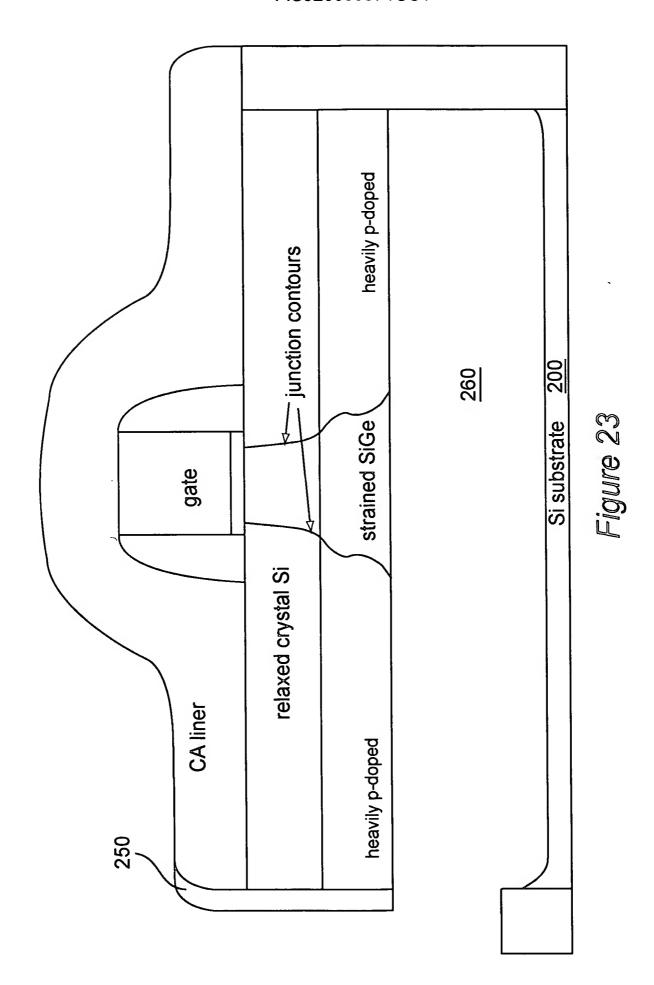


Figure 22

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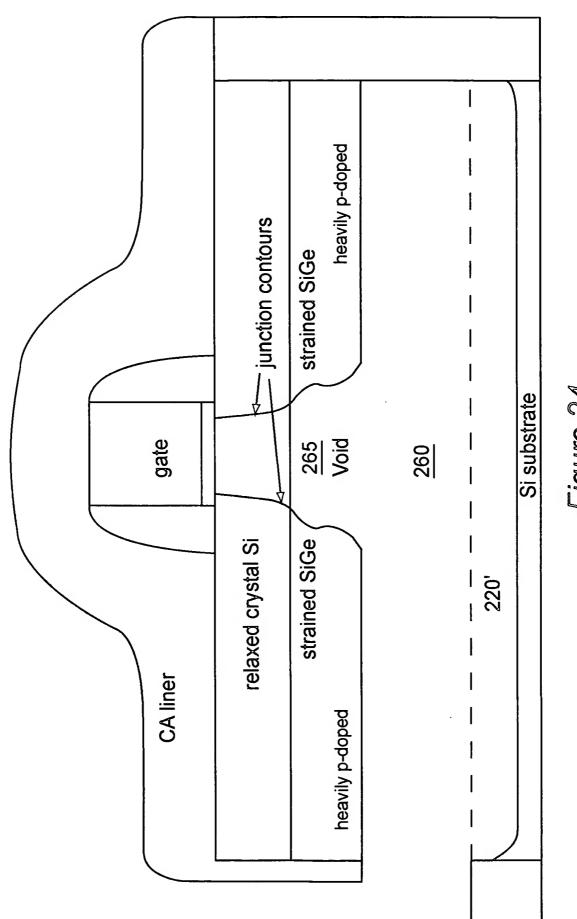


Figure 24

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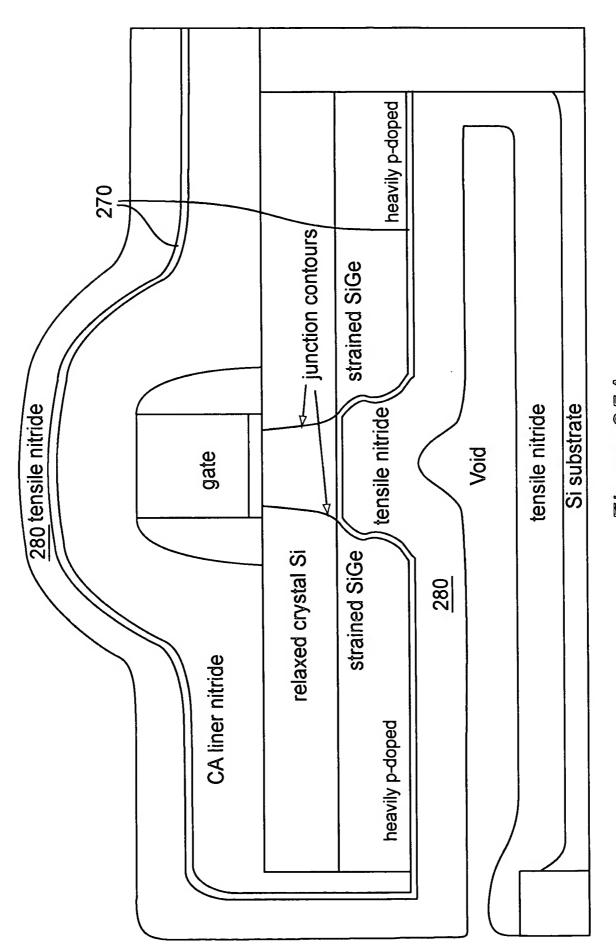


Figure 25A

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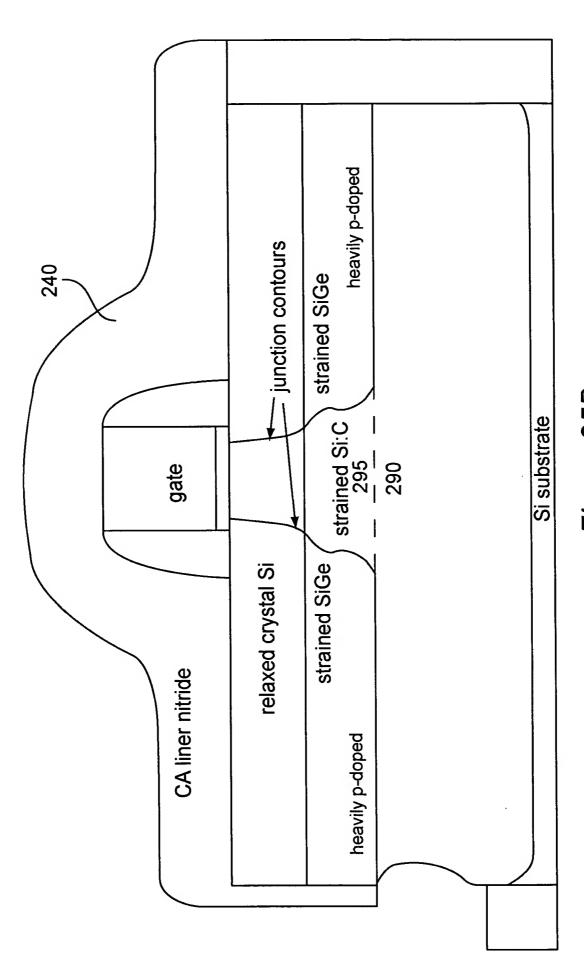


Figure 25B

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